

Quad 2-Input AND Gate in bare die form

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Description

The 74ACT08 quad 2-input AND gate is fabricated using a 1.5µm 5V CMOS process combining high speed LSTTL performance with CMOS low power. The device consists of four independent 2-input AND gates with standard push-pull outputs and performs the Boolean function Y = A \bullet B or Y = \overline{A} + \overline{B} . Device inputs are compatible with standard CMOS outputs and also directly compatible with LSTTL outputs. All inputs are protected against ESD and excess voltage transients.

Features:

- Inputs directly accept TTL
- Outputs directly interface CMOS, NMOS and TTL
- Outputs Source/Sink 24 mA
- Low Input Current: 1µA
- Functionally compatible with bipolar 74LS08
- Lower power alternative to bipolar logic.

Ordering Information

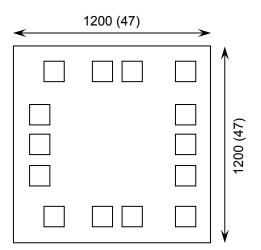
The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product please see

54ACT08

Die Dimensions in µm (mils)



Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Mechanical Specification

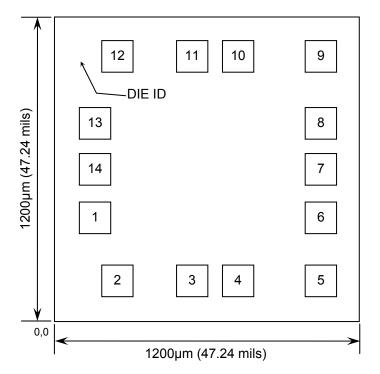
Die Cine (Unequin)	1200 x 1200	μm	
Die Size (Unsawn)	47 x 47	mils	
Minimum Bond Pad Size	120 x 120	μm	
Willimitati Bond Fad Size	4.72 x 4.72	mils	
Die Thickness	350 (±20)	μm	
Die Tilickiless	13.78 (±0.79)	mils	
Top Metal Composition	Al 1%Si 1.1μm		
Back Metal Composition	N/A – Bare Si		





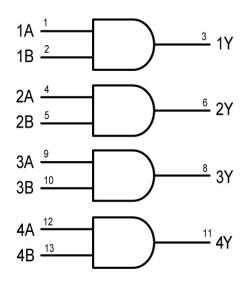
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Pad Layout and Functions



PAD	FUNCTION	COORDIN	ATES (µm)			
FAD	TONCTION	X	Y			
1	1A	150	350			
2	1B	150	100			
3	1Y	480	100			
4	2A	660	100			
5	2B	990	100			
6	2Y	990	350			
7	GND	990	540			
8	3Y	990	720			
9	3A	990	980			
10	3B	660	980			
11	4Y	480	980			
12	4A	150	980			
13	4B	100	720			
14	V _{CC}	100	540			
CONNECT CHIP BACK TO V _{CC} OR FLOAT						

Logic Diagram



Function Table

INP	UTS	OUTPUT
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н
H = F	liah leve	l (steady state)

H = High level (steady state)

L = Low level (steady state)





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Absolute Maximum Ratings¹

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V _{CC}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V _{IN}	-0.5 to V _{CC} +0.5	V
DC Output Voltage (Referenced to GND)	V _{OUT}	-0.5 to V _{CC} +0.5	V
DC Input Current	I _{IN}	±20	mA
DC Output Current, per pad	I _{OUT}	±50	mA
DC Supply Current, V _{CC} or GND, per pad	I _{CC}	±50	mA
Power Dissipation in Still Air ²	P _D	750	mW
Storage Temperature Range	T _{STG}	-65 to 150	°C

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages Referenced to GND)

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PARAMETER	SYMBOL	MIN	MAX	UNITS
DC Supply Voltage	V _{CC}	4.5	5.5	V
DC Input or Output Voltage	V _{IN} ,V _{OUT}	0	V _{CC}	V
Operating Temperature Range	TJ	-40	+85	°C
Output current - High	I _{OH}	-	-24	mA
Output current - Low	I _{OL}	-	24	mA
Input Rise or Fall rate V _{CC} = 4.5V	Δt/ΔV	0	10	ns/V
$(V_{IN} \text{ from } 0.8V \text{ to } 2V)$ $V_{CC} = 5.5V$	ΔυΔν	0	8	115/V

^{3.} This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range $GND \le (V_{IN} \text{ or } V_{OUT}) \le V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC Electrical Characteristics (Voltages referenced to GND)

PARAMETER	SYMBOL	V _{cc} CONDITIONS		LIMITS			UNITS
	OTHEOL	•66	GONDITIONS	25°C	85°C	FULL RANGE⁴	Oiiiio
Minimum High-Level	V _{IH}	4.5V	V _{OUT} = 0.1V	2	2	2	V
Input Voltage	V IH	5.5V	or V _{CC} -0.1V	2	2	2	V
Maximum Low-Level	V _{IL}	4.5V	$V_{OUT} = 0.1V$	0.8	0.8	0.8	V
Input Voltage	V IL	5.5V	or V _{CC} -0.1V	0.8	0.8	0.8	V
		4.5V	I _{OUT} = 50μA	0.1	0.1	0.1	V
		5.5V		0.1	0.1	0.1	
Minimum Low-Level	V _{OL}	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^5$	0.36	0.44	0.44	
Output Voltage	5.5\	5.5V	$I_{OL} = 24mA$	0.36	0.44	0.44	V
		4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^{5,6}$	-	-	1.65	V
		5.5V	$I_{OL} = 50 \text{mA}$	-	-	1.65	V

^{4.} -40° C $\leq T_{\text{J}} \leq +85^{\circ}$ C 5. All outputs loaded; thresholds on input associated with output under test. 6. Test time 1sec max, measurement made by forcing indicated current and measuring voltage to minimize power dissipation. Test verifies a minimum 75Ω transmission-line drive capability at 125° C





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DC Electrical Characteristics Continued (Voltages referenced to GND)

PARAMETER	SYMBOL	V _{cc} CONDITIONS			UNITS		
	OTHIDOL	STIMBSE VCC CONDITIONS	25°C	85°C	FULL RANGE⁴	Oitilo	
		4.5V	I _{OUT} = 50μA	4.4	4.4	4.4	V
Minimum High-Level	V _{OH}	5.5V	1001 – 30μΛ	5.4	5.4	5.4	V
Output Voltage	V OH	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^5$	3.86	3.76	3.76	V
		5.5V	I _{OH} = -24mA	4.86	4.76	4.76	v
Maximum Input Leakage Current	I _{IN}	5.5V	V _{IN} = V _{CC} or GND	±0.1	±1.0	±1.0	μA
Additional Maximum I _{CC} / Input	ΔI _{CCT}	5.5V	V _{IN} = V _{CC} -2.1V	0.6	1.5	1.5	mA
Minimum Dynamic	I _{OLD}	5.5V	V _{OLD} = 1.65V Max	-	75	75	mA
Output Current ⁷	I _{OHD}	5.5V	V _{OHD} = 3.85V Min	-	-75	-75	111/4
Maximum Quiescent Supply Leakage Current	I _{CC}	5.5V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	4	40	40	μА

^{7.} Maximum test duration 2ms, one output loaded at a time.

AC Electrical Characteristics⁸ V_{CC} = 5.0V ±0.5V

PARAMETER	SYMBOL	V _{cc}	CC CONDITIONS	LIMITS			UNITS	
	OTIMBOL Vec S	OONDITION	25°C	85°C	FULL RANGE⁴	Oili		
Maximum Propagation Delay	t _{PLH}	5.0V	C _L = 50pF,	9	10	10		
Input A or B to Output Y (Figure 1)	t _{PHL}	5.0V	Input tr = tf =3.0ns	9	10	10	ns	
Maximum Input	C _{IN}	5.0V	T _J = 25°C		TYPIC	AL	pF	
Capacitance	OIN	0.01	5.0V 1 _J - 25 C		4.5		Pi	
Power Dissipation Capacitance	C _{PD}	5.0V	$T_J = 25$ °C, $C_L = 50$ pF		20		pF	

^{8.} Not production tested in die form, characterized by chip design and tested in package.





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Switching Waveform

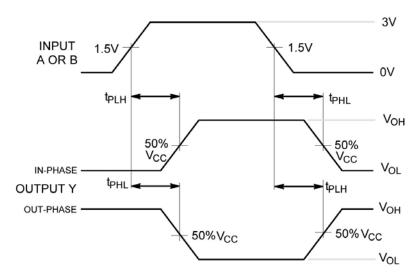


Figure 1 - Propagation Delay

Test Circuit $1k\Omega \nearrow R_{\text{pd}}$ OUTPUT C_{L}^* C_{L}^*

* Includes all probe and jig capacitance

Figure 2

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